

N-channel 40 V 2.2 mΩ standard level MOSFET in D2PAK

Rev. 1 — 20 March 2012

Product data sheet

1. Product profile

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1.1 General description

Standard level N-channel MOSFET in SOT404 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC convertors
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	306	W
Tj	junction temperature			-55	-	175	°C
Static cha	aracteristics						
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 25 A; T _j = 100 °C; see <u>Figure 6</u>	-	-	2.73	3.2	mΩ
		V_{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 6</u> ; see <u>Figure 13</u>		-	1.88	2.2	mΩ
Dynamic	characteristics						
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I _D = 25 A; V _{DS} = 20 V;		-	25	-	nC
Q _{G(tot)}	total gate charge	see Figure 14; see Figure 15		-	130	-	nC
Avalanch	e ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V}; \text{T}_{j(init)} = 25 ^\circ\text{C}; \\ \text{I}_{D} = 100 \text{ A}; \text{V}_{sup} \leq 40 \text{ V}; \text{ unclamped}; \\ \text{R}_{GS} = 50 \Omega \end{array} $		-	-	1.24	J

[1] Continuous current is limited by package

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain[1]	mb	
3	S	source		
mb	D	drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2

3. Ordering information

Table 3. Ordering information Type number Package Name Description Version PSMN2R2-40BS D2PAK plastic single-ended surface-mounted package (D2PAK); 3 leads SOT404 (one lead cropped)

4. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN2R2-40BS	PSMN2R2-40BS

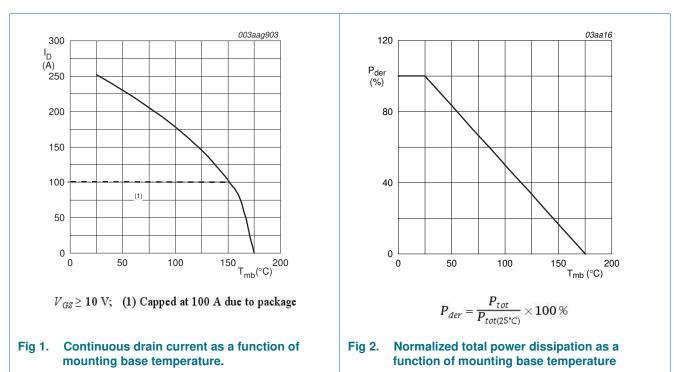
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

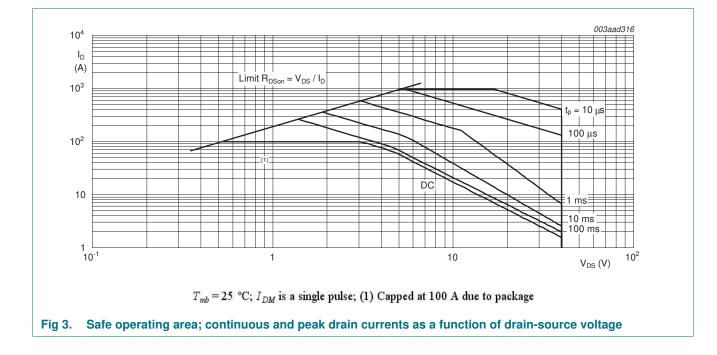
Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	40	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ		-	40	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3		-	962	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	306	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-dr	ain diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	962	А
Avalanche	ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le 40$ V; unclamped; R_{GS} = 50 Ω		-	1.24	J

[1] Continuous current is limited by package



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Thermal characteristics 6.

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.25	0.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum foot print; mounted in a printed circuit board	-	50	-	K/W

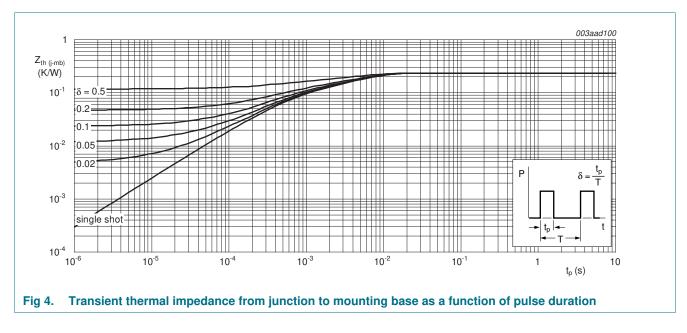


Table 6 Thermal characteristics

7. Characteristics

Table 7. Characteristics

Tested to JEDEC standards where applicable.

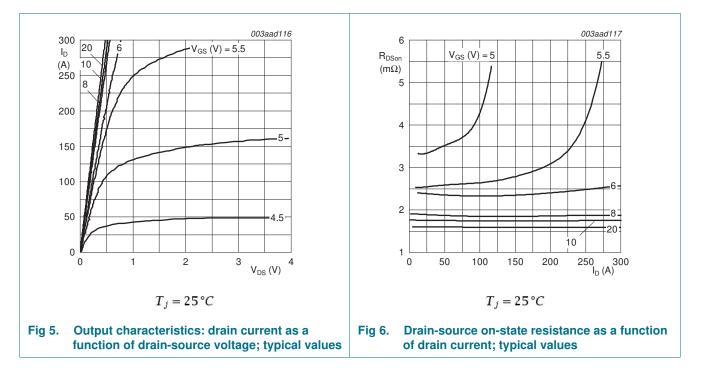
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = -55 \ ^\circ C$	36	-	-	V
		$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = 25 \ ^{\circ}C$	40	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 11</u>	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see Figure 11	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 11</u>	2	3	4	V
I _{DSS}	drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	10	μA
		V_{DS} = 40 V; V_{GS} = 0 V; T_j = 125 °C	-	-	200	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 25 A; T _j = 100 °C; see <u>Figure 6</u>	-	2.73	3.2	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see Figure 13; see Figure 6	-	3.76	4.4	mΩ
		V_{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 6</u> ; see <u>Figure 13</u>	-	1.88	2.2	mΩ
R _G	internal gate resistance (AC)	f = 1 MHz	-	1	-	Ω
Dynamic o	characteristics					
Q _{G(tot)}	total gate charge	$I_{D} = 0 \text{ A}; V_{DS} = 0 \text{V}; V_{GS} = 10 \text{V}$	-	110	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$	-	130	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	42	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	24	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	18	-	nC
Q _{GD}	gate-drain charge		-	25	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15}$	-	4.95	-	V
C _{iss}	input capacitance	$V_{DS} = 20 V; V_{GS} = 0 V; f = 1 MHz;$	-	8423	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{16}$	-	1671	-	pF
C _{rss}	reverse transfer capacitance		-	814	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 20 \text{ V}; \text{ R}_{L} = 0.25 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	33.2	-	ns
t _r	rise time	$R_{G(ext)} = 1.5 \Omega$	-	40.4	-	ns
t _{d(off)}	turn-off delay time		-	66.6	-	ns
t _f	fall time		-	25.2	-	ns

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Table 7. Characteristics ...continued

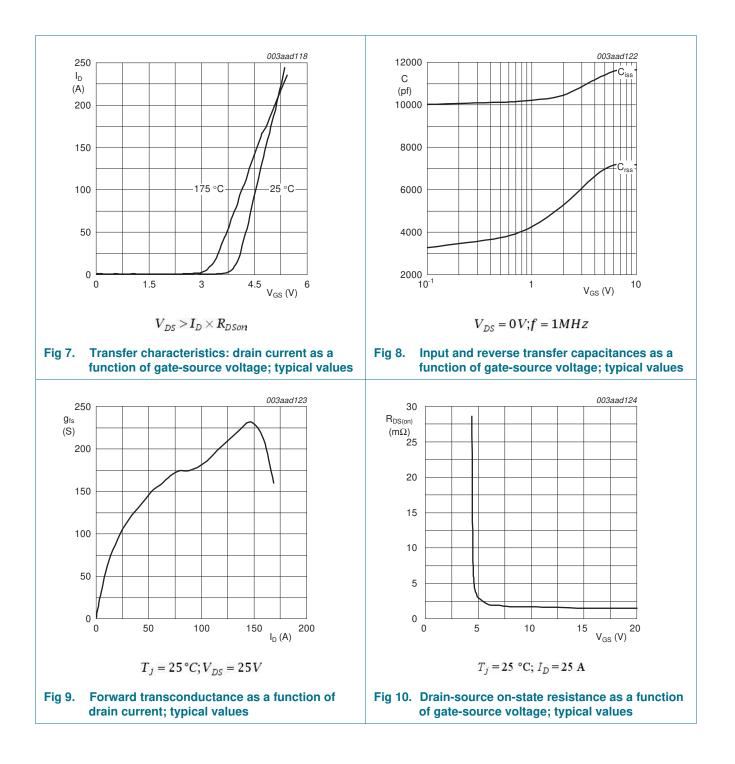
Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dr	ain diode				-	
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$ $V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}$	-	53.7	-	ns
Qr	recovered charge	I _S = 25 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = 20 V; T _j = 25 °C	-	80.75	-	nC



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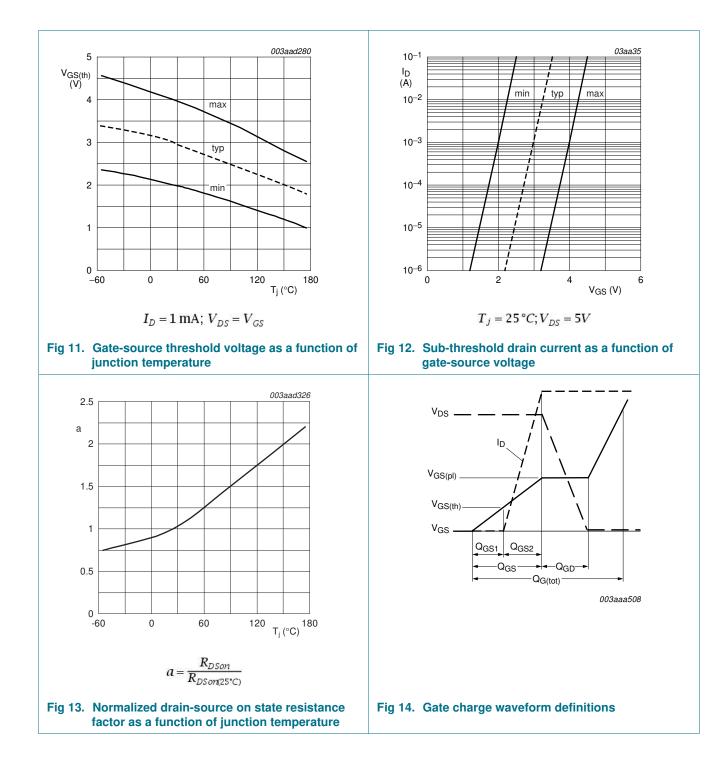
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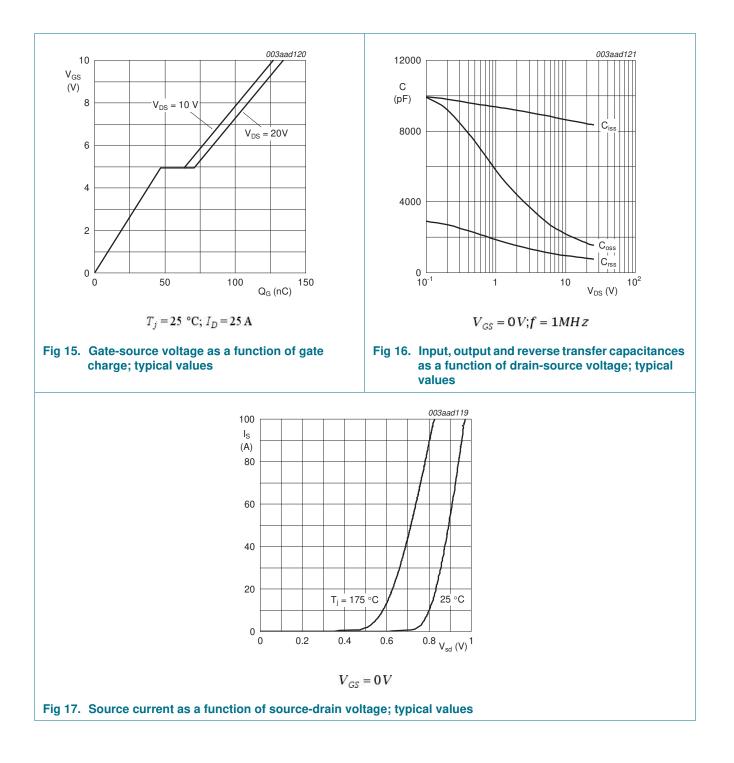
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8. Package outline

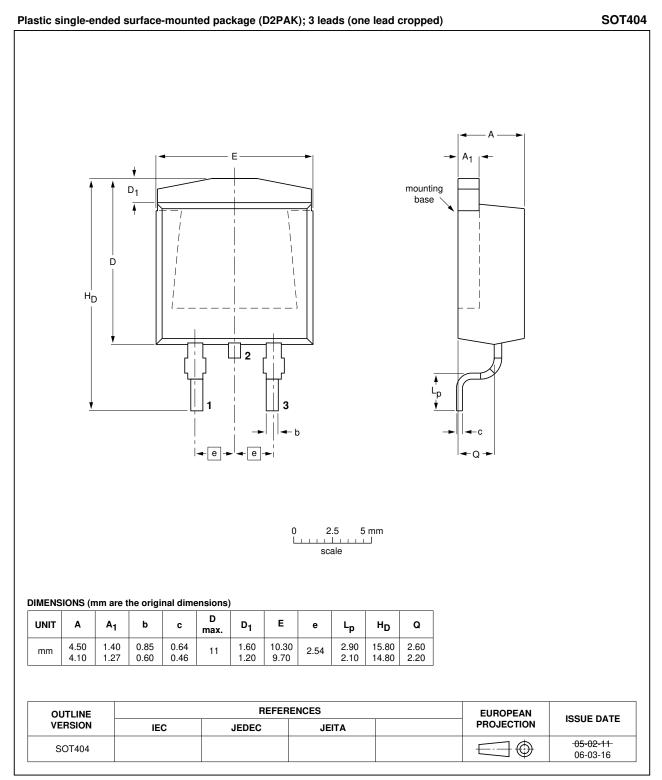


Fig 18. Package outline SOT404 (D2PAK)

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PSMN2R2-40BS

9. Revision history

Table 8. Revision h	Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
PSMN2R2-40BS v.1	20120320	Product data sheet	-	-			

10. Legal information

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Document status[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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